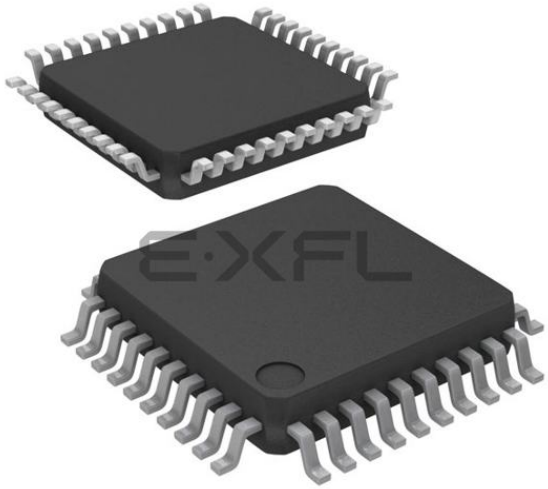
Renesas Electronics America Inc - R5F212G4SNFP#W4 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	8MHz
Connectivity	LINbus, SIO, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	27
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f212g4snfp-w4

1. Overview

1.1 Features

The R8C/2G Group of single-chip MCUs incorporates the R8C/Tiny Series CPU core, employing sophisticated instructions for a high level of efficiency. With 1 Mbyte of address space, and it is capable of executing instructions at high speed. In addition, the CPU core boasts a multiplier for high-speed operation processing.
Power consumption is low, and the supported operating modes allow additional power control. These MCUs also use an anti-noise configuration to reduce emissions of electromagnetic noise and are designed to withstand EMI.
Integration of many peripheral functions, including multifunction timer and serial interface, reduces the number of system components.

1.1.1 Applications

Electric power meters, electronic household appliances, office equipment, audio equipment, consumer equipment, etc.

1.1.2 Specifications

Table 1.1 outlines the Specifications for R8C/2G Group.

Table 1.1 Specifications for R8C/2G Group

Item	Function	Specification
CPU	Central processing unit	R8C/Tiny series core • Number of fundamental instructions: 89 • Minimum instruction execution time: 125 ns (System clock = 8 MHz, VCC = 2.7 to 5.5 V) 250 ns (System clock = 4 MHz, VCC = 2.2 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM	Refer to **Table 1.2 Product List for R8C/2G Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3
Comparator		• 2 circuits (shared with voltage monitor 1 and voltage monitor 2) • External reference voltage input is available
I/O Ports		• Output-only: 1 • CMOS I/O ports: 27, selectable pull-up resistor
Clock	Clock generation circuits	• 2 circuits: On-chip oscillator (high-speed, low-speed) (high-speed on-chip oscillator has a frequency adjustment function), XCIN clock oscillation circuit (32 kHz) • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• External: 5 sources, Internal: 17 sources, Software: 4 sources • Priority levels: 7 levels
Watchdog Timer		15 bits × 1 (with prescaler), reset start selectable
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode
	Timer RF	16 bits × 1 (with capture/compare register pin and compare register pin) Input capture mode, output compare mode
Serial Interface	UART0, UART2	Clock synchronous serial I/O/UART × 2
LIN Module		Hardware LIN: 1 (timer RA, UART0)
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 100 times • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function
Operating Frequency/Supply Voltage		System clock = 8 MHz (VCC = 2.7 to 5.5 V) System clock = 4 MHz (VCC = 2.2 to 5.5 V)
Current consumption		5 mA (VCC = 5 V, system clock = 8 MHz) 23 μA (VCC = 3 V, wait mode (low-speed on-chip oscillator on)) 0.7 μA (VCC = 3 V, stop mode, BGR trimming circuit disabled)
Operating Ambient Temperature		-20 to 85°C (N version) -40 to 85°C (D version)(1)
Package		32-pin LQFP Package code: PLQP0032GB-A (previous code: 32P6U-A)

NOTE:
1. Specify the D version if D version functions are to be used.

1.2 Product List

Table 1.2 lists Product List for R8C/2G Group, Figure 1.1 shows a Part Number, Memory Size, and Package of R8C/2G Group.

Table 1.2 Product List for R8C/2G Group **Current of Apr. 2008**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F212G4SNFP	16 Kbytes	512 bytes	PLQP0032GB-A	N version
R5F212G5SNFP	24 Kbytes	1 Kbytes	PLQP0032GB-A	
R5F212G6SNFP	32 Kbytes	1 Kbytes	PLQP0032GB-A	
R5F212G4SDFP	16 Kbytes	512 bytes	PLQP0032GB-A	D version
R5F212G5SDFP	24 Kbytes	1 Kbytes	PLQP0032GB-A	
R5F212G6SDFP	32 Kbytes	1 Kbytes	PLQP0032GB-A	

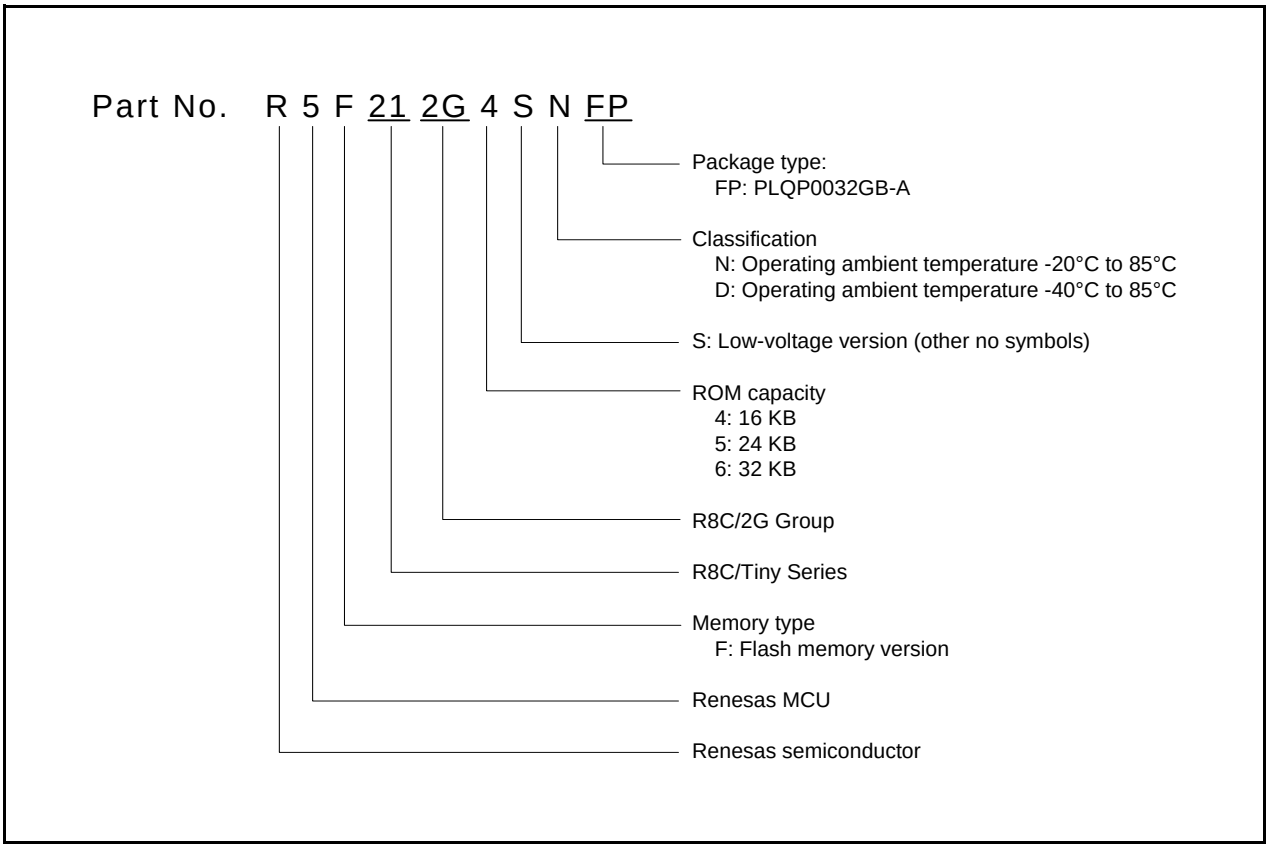


Figure 1.1 Part Number, Memory Size, and Package of R8C/2G Group

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

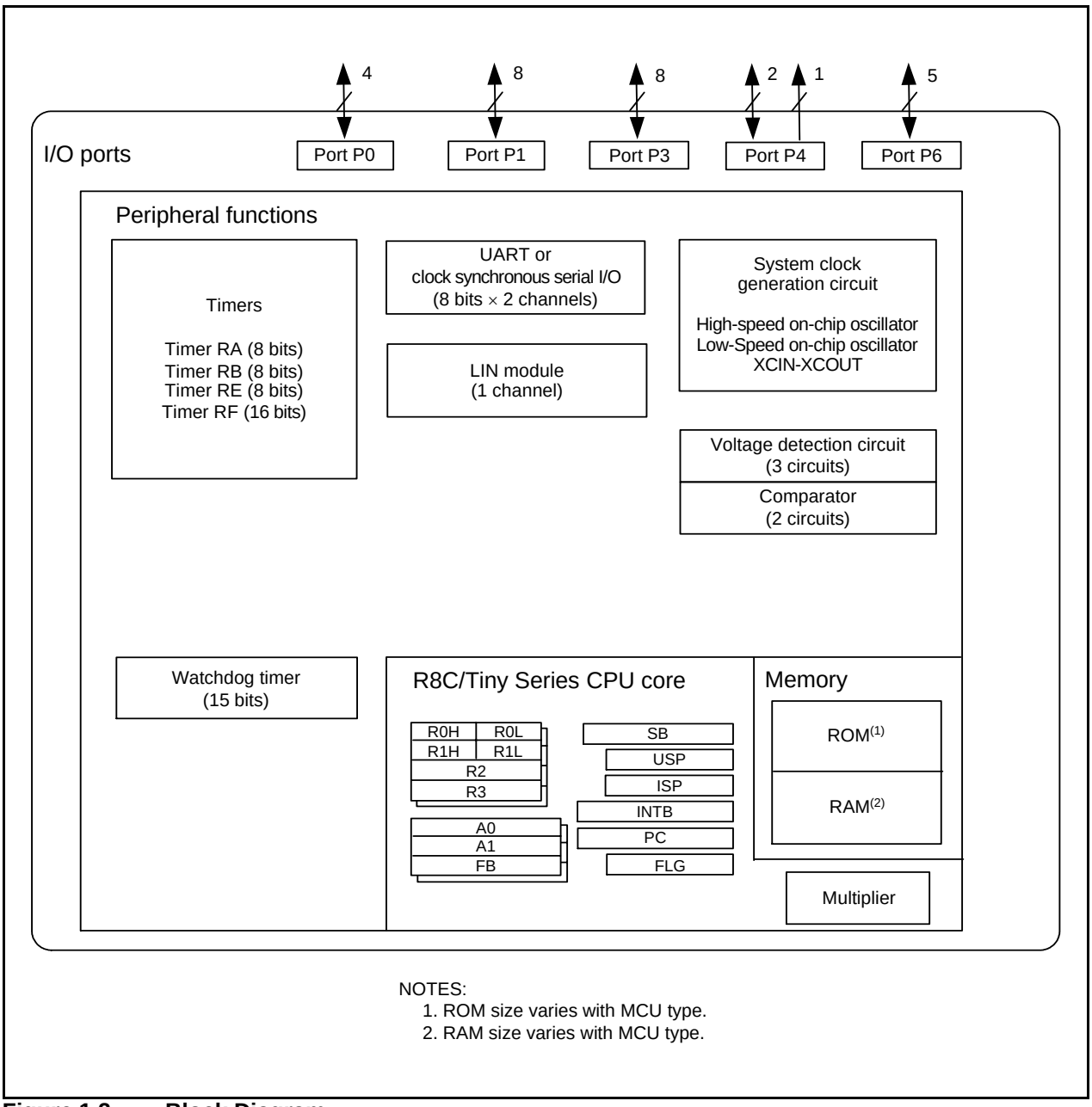


Figure 1.2 Block Diagram

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupt are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide and assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h			
0089h			
008Ah			
008Bh			
008Ch			
008Dh			
008Eh			
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h			
00A9h			
00AAh			
00ABh			
00ACh			
00ADh			
00AEh			
00AFh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.7 SFR Information (7)(1)

Address	Register	Symbol	After reset
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			

X: Undefined
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 4.11 SFR Information (11)[1]

Address	Register	Symbol	After reset
0270h			
0271h			
0272h			
0273h			
0274h			
0275h			
0276h			
0277h			
0278h			
0279h			
027Ah			
027Bh			
027Ch			
027Dh			
027Eh			
027Fh			
0280h			
0281h			
0282h			
0283h			
0284h			
0285h			
0286h			
0287h			
0288h			
0289h			
028Ah			
028Bh			
028Ch			
028Dh			
028Eh			
028Fh			
0290h	Timer RF Register	TRF	00h
0291h			00h
0292h			
0293h			
0294h			
0295h			
0296h			
0297h			
0298h			
0299h	Timer RF Control Register 2	TRFCR2	00h
029Ah	Timer RF Control Register 0	TRFCR0	00h
029Bh	Timer RF Control Register 1	TRFCR1	00h
029Ch	Capture and Compare 0 Register	TRFM0	0000h[2]
029Dh			FFFFh[3]
029Eh	Compare 1 Register	TRFM1	FFh
029Fh			FFh
02A0h			
02A1h			
02A2h			
02A3h			
02A4h			
02A5h			
02A6h			
02A7h			
02A8h			
02A9h			
02AAh			
02ABh			
02ACh			
02ADh			
02AEh			
02AFh			

X: Undefined
NOTES:
1. The blank regions are reserved. Do not access locations in these regions.
2. After input capture mode.
3. After output compare mode.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version) / –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply voltage			2.2	–	5.5	V
V_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	–80	mA
$I_{OH(peak)}$	Peak output “H” current	All pins		–	–	–10	mA
$I_{OH(avg)}$	Average output “H” current	All pins		–	–	–5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” currents	Sum of all pins $I_{OL(avg)}$		–	–	80	mA
$I_{OL(peak)}$	Peak output “L” currents	All pins		–	–	10	mA
$I_{OL(avg)}$	Average output “L” current	All pins		–	–	5	mA
$f_{(XCIN)}$	XCIN clock input oscillation frequency		2.2 V ≤ V_{CC} ≤ 5.5 V	0	–	70	kHz
–	System clock	OCD2 = 0 XCIN clock selected	2.2 V ≤ V_{CC} ≤ 5.5 V	0	–	70	kHz
		OCD2 = 1 On-chip oscillator clock selected	HRA01 = 0 Low-speed on-chip oscillator selected	–	125	–	kHz
			HRA01 = 1 High-speed on-chip oscillator selected 2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	8	MHz
			HRA01 = 1 High-speed on-chip oscillator selected 2.2 V ≤ V_{CC} ≤ 5.5 V	–	–	4	MHz

NOTES:
1. V_{CC} = 2.2 to 5.5 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

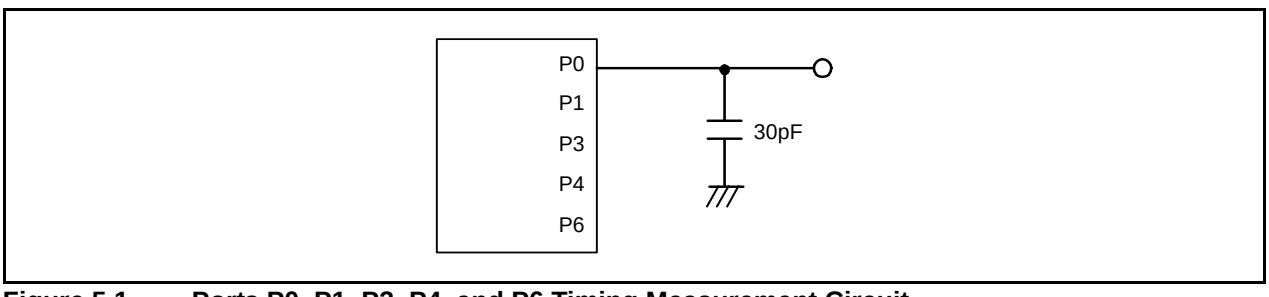


Figure 5.1 Ports P0, P1, P3, P4, and P6 Timing Measurement Circuit

Table 5.3 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		100(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.4 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.5 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(4)		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.6 Voltage Detection 2 Circuit Electrical Characteristics

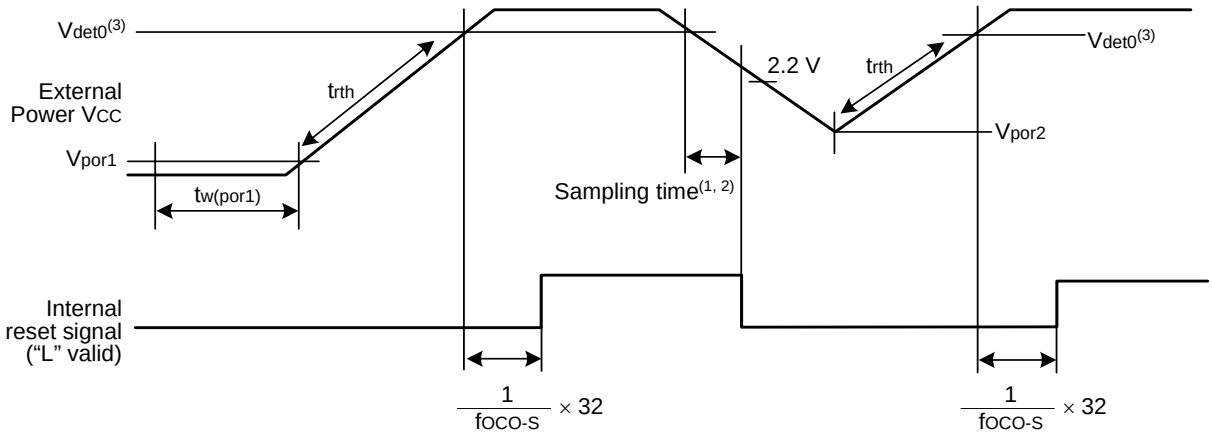
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.7 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V_{det0}	V
t_{rth}	External power V_{CC} rise gradient(2)		20	–	–	mV/msec

NOTES:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if $V_{CC} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if –20°C ≤ T_{opr} ≤ 85°C, maintain $t_{w(por1)}$ for 3,000 s or more if –40°C ≤ T_{opr} < –20°C.



NOTES:
1. When using the voltage monitor 0 digital filter, ensure that the voltage is within the MCU operation voltage range (2.2 V or above) during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.2 Reset Circuit Electrical Characteristics

Table 5.8 Comparator Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vref	Internal reference voltage	V_{CC} = 2.2 V to 5.5 V, T_{opr} = 25°C	1.15	1.25	1.35	V
		V_{CC} = 2.2 V to 5.5 V, T_{opr} = –40 to 85°C	–	1.25	–	V
Vcref	External input reference voltage	V_{CC} = 2.2 V to 4.0 V	0.5	–	V_{CC} – 1.1	V
		V_{CC} = 4.0 V to 5.5 V	0.5	–	V_{CC} – 1.5	
Vcin	External comparison voltage input range		–0.3	–	V_{CC} + 0.3	V
Vofs	Input offset voltage		–	20	120	mV
Tcrsp	Response time		–	4	–	µs

NOTE:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.9 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-F	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V, T_{opr} = 0 to 60°C(2)	7.76	8	8.24	MHz
		V_{CC} = 2.7 V to 5.5 V, T_{opr} = –20 to 85°C(2)	7.68	8	8.32	MHz
		V_{CC} = 2.7 V to 5.5 V, T_{opr} = –40 to 85°C(2)	7.44	8	8.32	MHz
		V_{CC} = 2.2 V to 5.5 V, T_{opr} = –20 to 85°C(3)	7.04	8	8.96	MHz
		V_{CC} = 2.2 V to 5.5 V, T_{opr} = –40 to 85°C(3)	6.8	8	9.2	MHz

NOTES:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the HRA1 register is set to the value before shipment and the HRA2 register is set to 00h.
3. These standard values show when the correction value in the FRA6 register is written into the HRA1 register.

Table 5.10 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.13 Electrical Characteristics (2) [Vcc = 5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed on-chip oscillator mode	High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5	8	mA
			High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		Low-speed on-chip oscillator mode	High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Low-speed clock mode	High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) FMR47 = 1	–	130	300	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA
		Wait mode	High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	75	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	60	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit disabled (BGRCR0 = 1)	–	4	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit disabled (BGRCR0 = 1)	–	2.2	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit enabled (BGRCR0 = 0)	–	8	–	µA
			High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1 BGR trimming circuit enabled (BGRCR0 = 0)	–	6	–	µA
		Stop mode	XCIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit disabled (BGRCR0 = 1)	–	0.8	3	µA
			XCIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit disabled (BGRCR0 = 1)	–	1.2	–	µA
			XCIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit enabled (BGRCR0 = 0)	–	5	8	µA
			XCIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0 BGR trimming circuit enabled (BGRCR0 = 0)	–	5.5	–	µA

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.14 XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

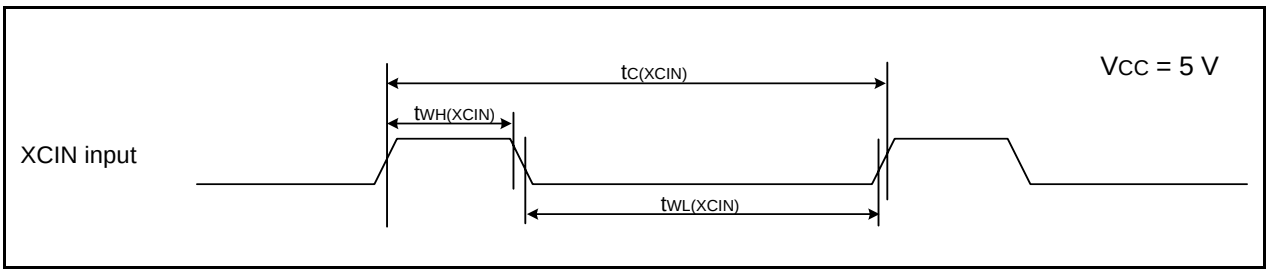


Figure 5.3 XCIN Input Timing Diagram when V_{CC} = 5 V

Table 5.15 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

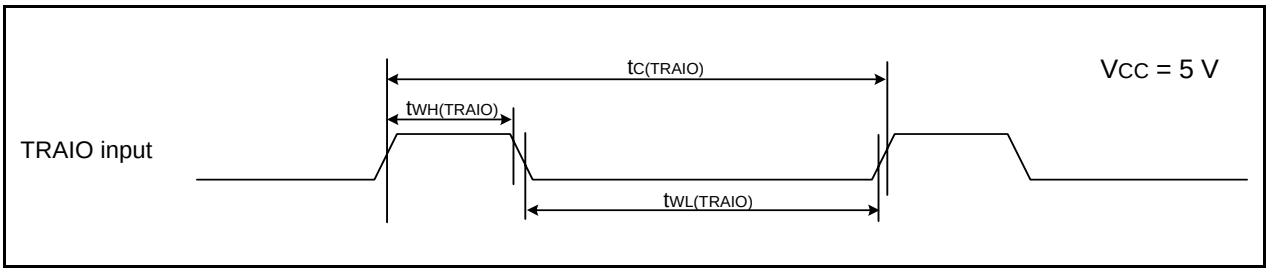


Figure 5.4 TRAIO Input Timing Diagram when V_{CC} = 5 V

Table 5.16 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 2

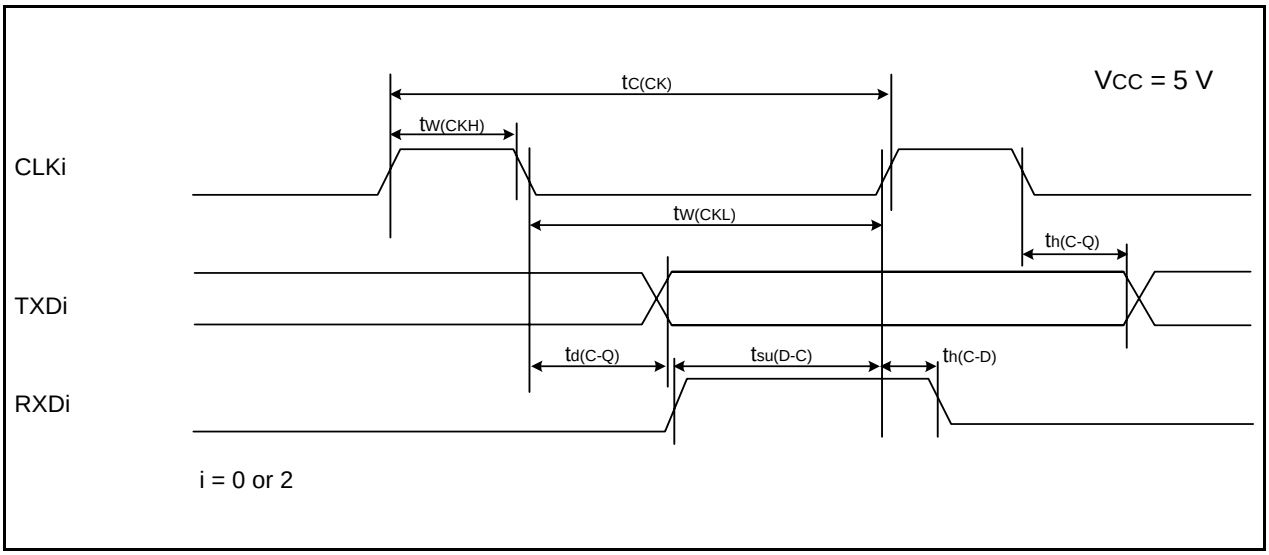


Figure 5.5 Serial Interface Timing Diagram when VCC = 5 V

Table 5.17 External Interrupt $\overline{INTi}$ (i = 0, 1, 2, 4) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

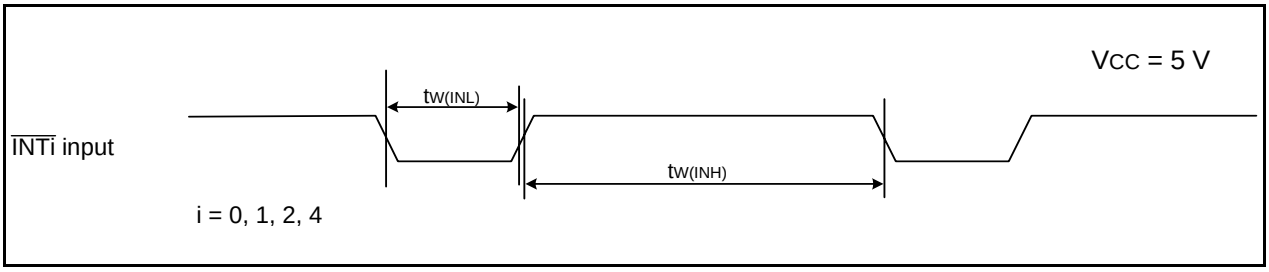


Figure 5.6 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 5 V

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 3 V]

Table 5.20 XCIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

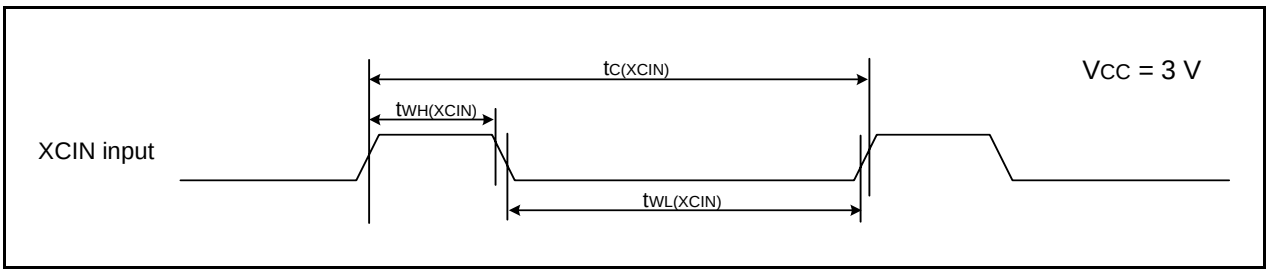


Figure 5.7 XCIN Input Timing Diagram when V_{CC} = 3 V

Table 5.21 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

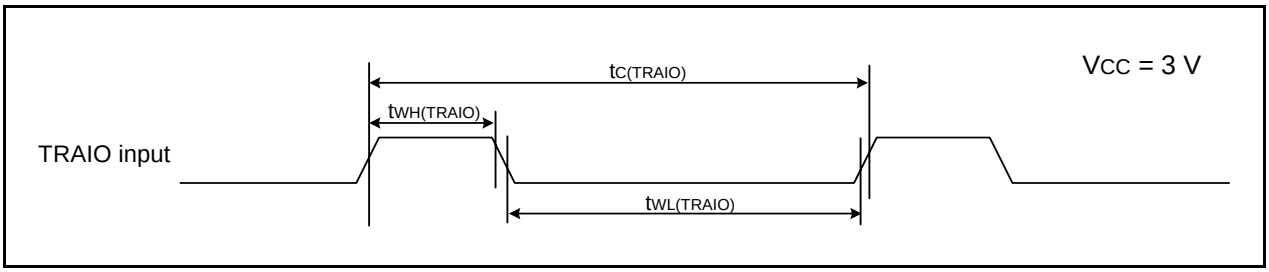


Figure 5.8 TRAIO Input Timing Diagram when V_{CC} = 3 V

Table 5.24 Electrical Characteristics (5) [V_{CC} = 2.2 V]

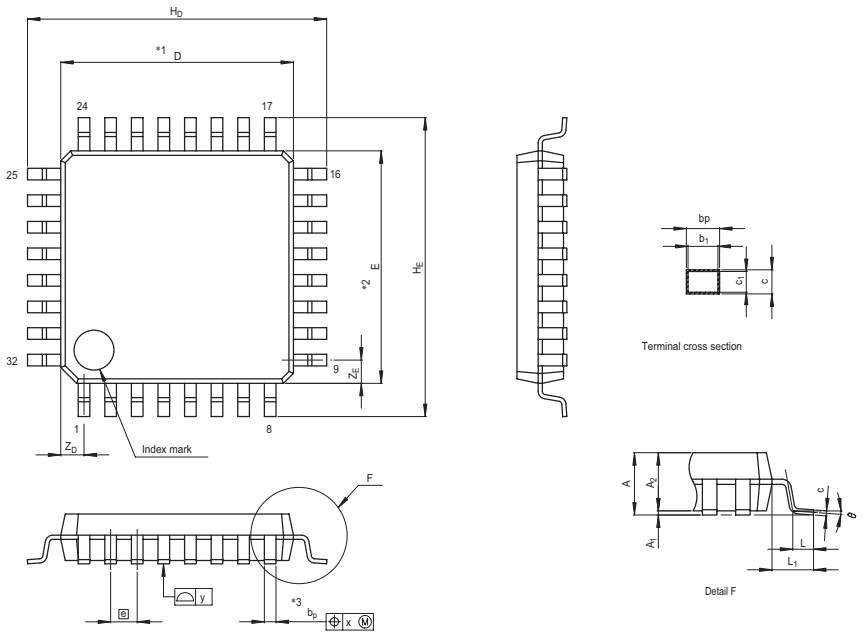
Symbol	Parameter		Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	Output “H” voltage		I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage		I_{OL} = 1 mA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, RXD0, RXD2, CLK0, CLK2		0.05	0.3	–	V
		$\overline{RESET}$		0.05	0.15	–	V
I_{IH}	Input “H” current		VI = 2.2 V	–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V	–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V	100	200	600	kΩ
R_{fXCIN}	Feedback resistance	XCIN		–	35	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode	1.8	–	–	V

NOTE:
1. V_{CC} = 2.2 V at T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.

Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP32-7x7-0.80	PLQP0032GB-A	32P6U-A	0.2g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.32	0.37	0.42
b_1	—	0.35	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.8	—
x	—	—	0.20
y	—	—	0.10
Z_D	—	0.7	—
Z_E	—	0.7	—
L	0.3	0.5	0.7
L_1	—	1.0	—

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Colophon .7.2